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Rev.A Sep.-2021

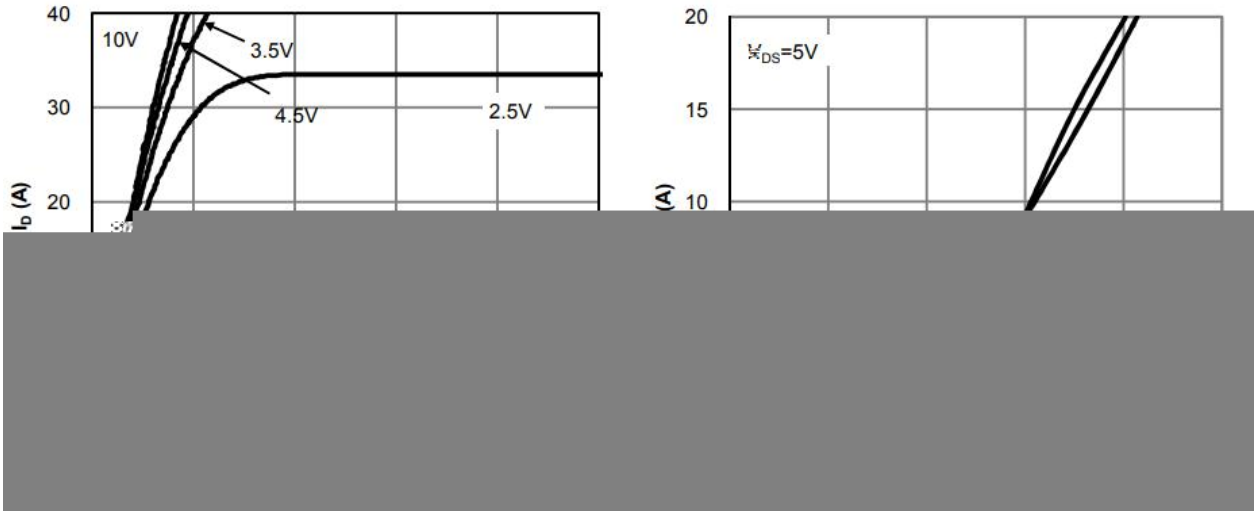
SOT23-3 N MOS

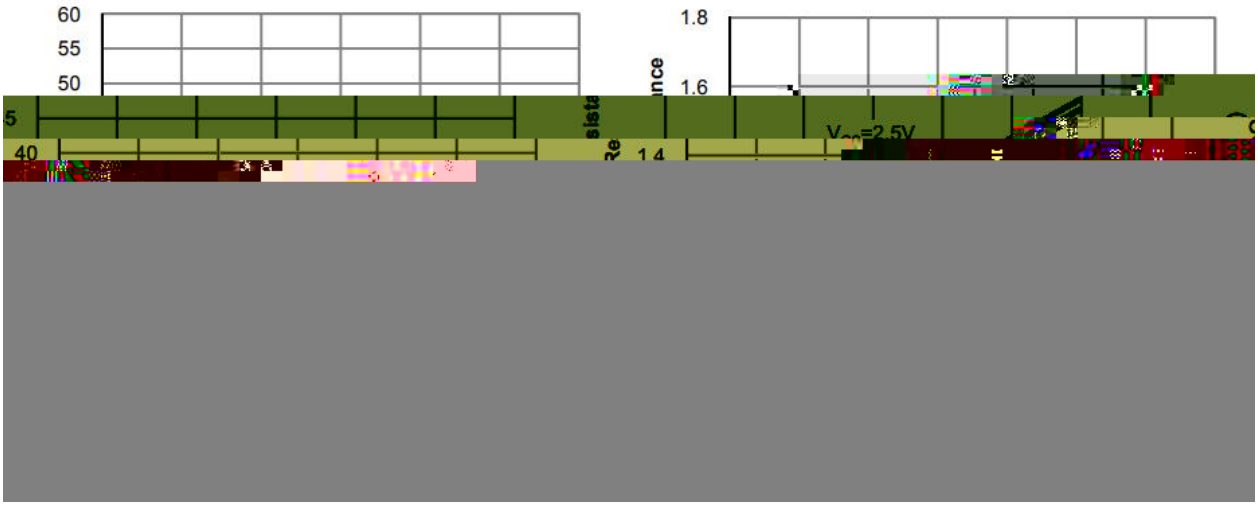
- CHANNEL MOSFET in a SOT23-3 Plastic Package.

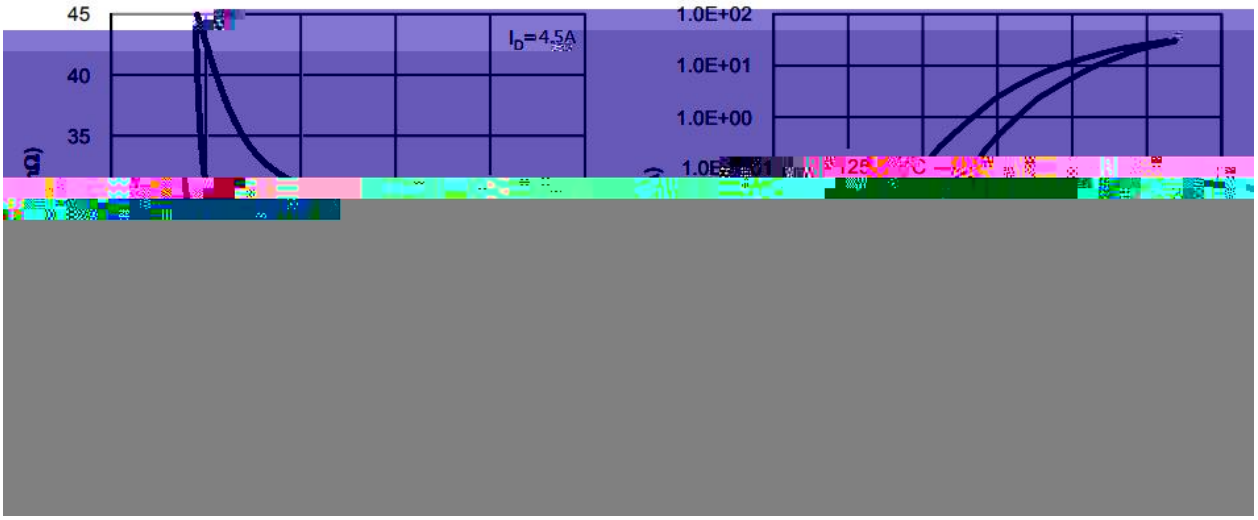
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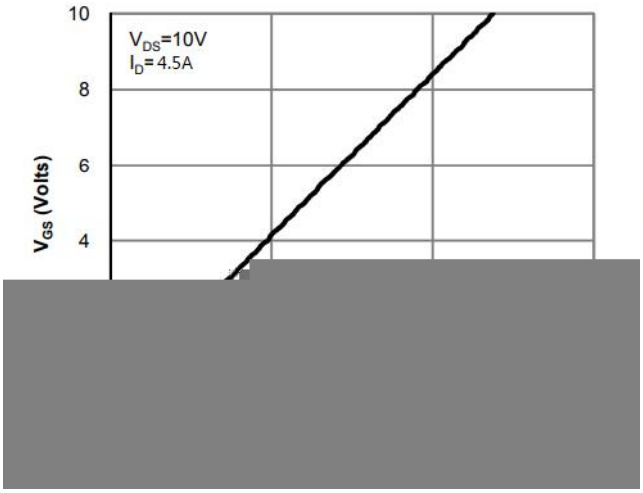
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V_{GSS}	±10	V
Drain Current – Continuous		I_D	4.5	A
Pulsed Drain Current		I_{DM}	12	A
Power Dissipation		P_D	1.4	W
Storage Temperature Range		T_{stg}	-55～150	℃
Maximum Junction-to-Ambient	t ≤ 10s	$R_{\theta JA}$	90	℃/W
Maximum Junction-to-Ambient				

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Total Gate Charge	Qg(10V)	V_{GS}=10V, V_{DS}=10V I_D=4.5A		12.5		nC
Total Gate Charge	Qg(4.5V)			6		
Gate Source Charge	Qgs			1		
Gate Drain Charge	Qgd			2		
Turn–On Delay Time	$t_{d(on)}$	V_{GS}=10V, V_{DS}=10V R_{GEN}=3Ω R_L=1.7Ω		3		ns
Turn–On Rise Time	t_r			7.5		
Turn–Off Delay Time	$t_{d(off)}$			20		
Turn–Off Fall Time	t_f			6		


40
30
20
10V
3.5V
4.5V
2.5V
I_D (A)
20
15
10
V_{DS}=5V
(A)


60
55
50
40
1.8
1.6
1.4
V_{GS}=2.5V


45
40
35
I_D=4.5A
1.0E+02
1.0E+01
1.0E+00
125°C



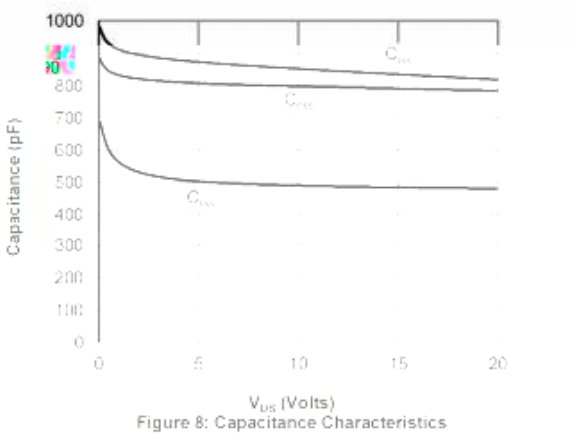
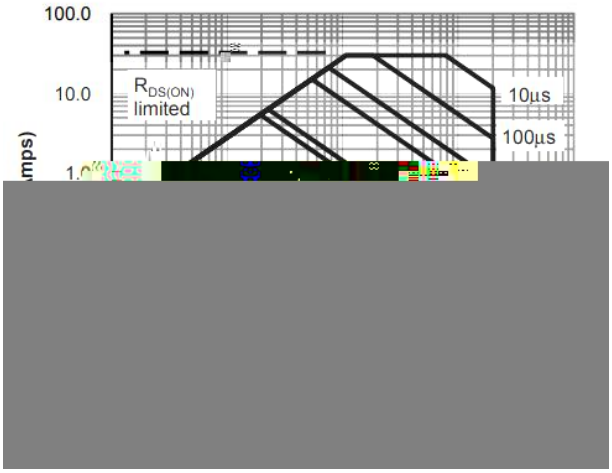
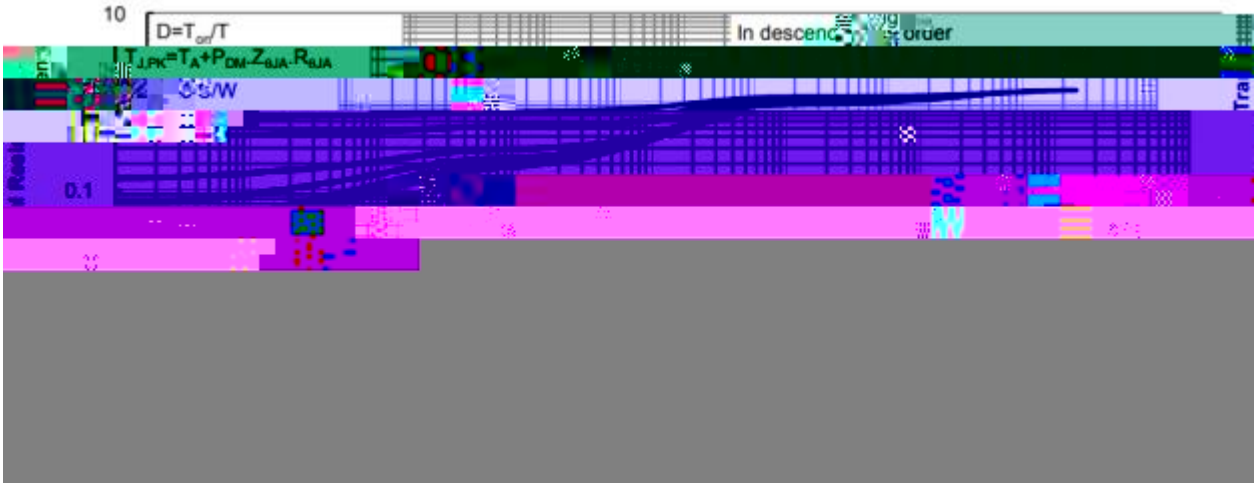
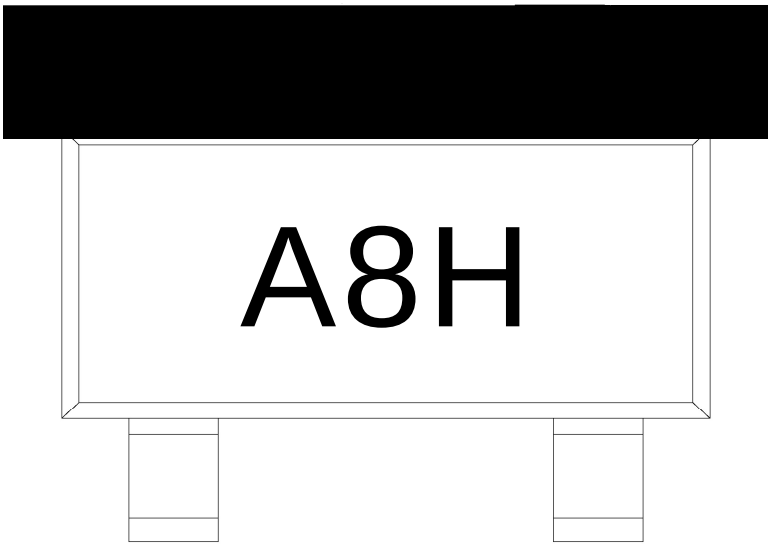


Figure 8: Capacitance Characteristics







A8:

H:

Note:

A8	Product Type Code
H:	Company Code.

Temperature Profile for IR Reflow Soldering(Pb-Free)

Note:

1 150